BC808 TRANSISTOR (PNP)

1.BASE
2.COLLECTOR
3.EMITTER

SOT-23-3

FEATURES

- Suitable for AF-Driver stages and low power output stages
- Complement to BC818

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.8	A
P_{C*}	Collector Power Dissipation	300	mW
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-25V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-100mA	100		630	
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-300mA	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-0.7	V
Base-emitter voltage	V_{BE}	V_{CE}=-1V, I_C=-300mA			-1.2	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA, f=50MHz		100		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		12		pF

CLASSIFICATION OF h_{FE}

Rank	16	25	40
Range $h_{FE(1)}$	100-250	160-400	250-630
Marking	5E	5F	5G